

2.5V Drive Nch MOSFET

RSM002N06

Structure

Silicon N-channel MOSFET

Features

1) High speed switing.

- 2) Small package(VMT3).
- 3) Low voltage drive(2.5V drive).

Application

Switching

Packaging specifications

	Package	Taping
Туре	Code	T2L
	Basic ordering unit (pieces)	8000
RSM002N0	06	0

• Absolute maximum ratings (Ta = 25°C)

Param	eter	Symbol	Limits	Unit
Drain-source voltage		V _{DSS}	60	V
Gate-source voltage		V_{GSS}	±20	V
Drain current	Continuous	I _D	±250	mA
	Pulsed	I _{DP} *1	±1	А
Source current	Continuous	I _S	125	mA
(Body Diode)	Pulsed	الا ال	1	А
Power dissipation		P _D *2	150	mW
Channel temperature		Tch	150	°C
Range of storage tem	perature	Tstg	-55 to +150	°C

*1 Pw≤10μs, Duty cycle≤1%

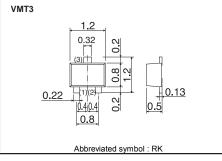
*2 Each terminal mounted on a recommended land.

• Thermal resistance

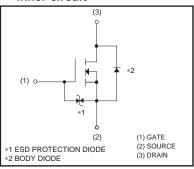
Parameter	Symbol	Limits	Unit
Channel to ambient	Rth (ch-a)*	833	°C / W

* Each terminal mounted on a recommended land.

• Dimensions (Unit : mm)



• Inner circuit



•Electrical characteristics (Ta = 25°C)

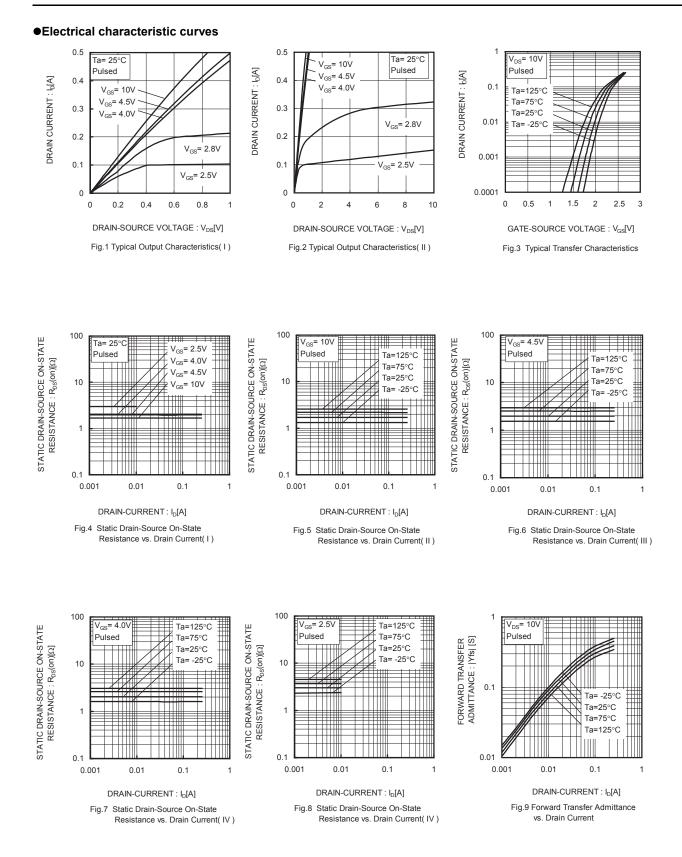
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Gate-source leakage	I _{GSS}	-	-	±10	μA	V _{GS} =±20V, V _{DS} =0V
Drain-source breakdown voltage	V _{(BR)DSS}	60	-	-	V	I _D =1mA, V _{GS} =0V
Zero gate voltage drain current	I _{DSS}	-	-	1	μA	V _{DS} =60V, V _{GS} =0V
Gate threshold voltage	V _{GS (th)}	1.0	-	2.3	V	V _{DS} =10V, I _D =1mA
		-	1.7	2.4	$\begin{array}{c} 3.0 \\ 3.2 \\ 12.0 \end{array} \Omega \begin{array}{c} I_{D} = 250 \text{mA}, V_{GS} = 4.5 \text{N} \\ I_{D} = 250 \text{mA}, V_{GS} = 4.0 \text{N} \\ I_{D} = 10 \text{mA}, V_{GS} = 2.5 \text{V} \end{array}$	I _D =250mA, V _{GS} =10V
Static drain-source on-state	P*	-	2.1	3.0		
resistance	R _{DS (on)}	-	2.3	3.2	52	I _D =250mA, V _{GS} =4.0\
		-	3.0	12.0		I _D =10mA, V _{GS} =2.5V
Forward transfer admittance	I Y _{fs} I*	0.25	-	-	S	I _D =250mA, V _{DS} =10V
Input capacitance	C _{iss}	-	15	-	pF	V _{DS} =25V
Output capacitance	C _{oss}	-	4.5	-	pF	V _{GS} =0V
Reverse transfer capacitance	C _{rss}	-	2.0	-	pF	f=1MHz
Turn-on delay time	t _{d(on)} *	-	3.5	-	ns	I _D =100mA, V _{DD} ≒ 30V
Rise time	t _r *	-	5	-	ns	V _{GS} =10V
Turn-off delay time	t _{d(off)} *	-	18	-	ns	R _L ≒300Ω
Fall time	t _f *	-	28	-	ns	R _G =10Ω

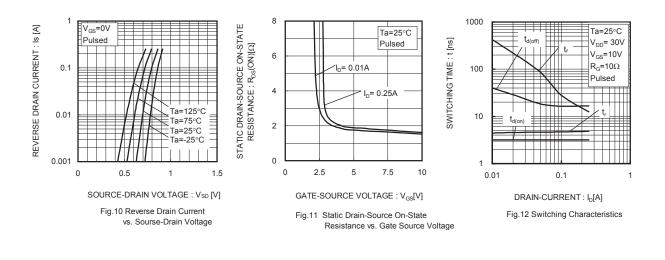
*Pulsed

•Body diode characteristics (Source-Drain) (Ta = 25°C)

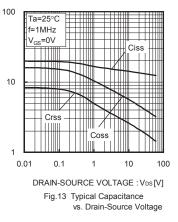
Parameter	Symbol	Min.	Тур.	Max.	Unit	Conditions
Forward voltage	V_{SD}^{*}	-	-	1.2	V	I _s =250mA, V _{GS} =0V

*Pulsed





CAPACITANCE : C [pF]



Measurement circuits

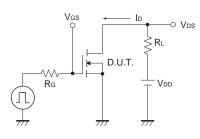


Fig.1-1 Switching time measurement circuit

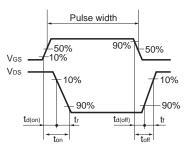


Fig.1-2 Switching waveforms

Notice

This product might cause chip aging and breakdown under the large electrified environment. Please consider to design ESD protection circuit.

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